











SN74LVC2G00

SCES193N - APRIL 1999-REVISED JANUARY 2015

# SN74LVC2G00 Dual 2-Input Positive-NAND Gate

#### **Features**

- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V<sub>CC</sub> Operation
- Inputs Accept Voltages to 5.5 V
- Max  $t_{pd}$  of 4.3 ns at 3.3 V
- Low Power Consumption, 10- $\mu$ A Max I<sub>CC</sub>
- ±24-mA Output Drive at 3.3 V
- Typical V<sub>OLP</sub> (Output Ground Bounce)  $< 0.8 \text{ V at V}_{CC} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}$
- Typical V<sub>OHV</sub> (Output V<sub>OH</sub> Undershoot) > 2 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C
- I<sub>off</sub> Supports Live Insertion, Partial Power Down Mode, and Back Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Protection Exceeds JESD 22
  - 2000-V Human-Body Model
  - 1000-V Charged-Device Model

# 2 Applications

- IP Phones: Wired and Wireless
- **Optical Modules**
- Optical Networking: EPON and Video Over Fiber
- Point-to-Point Microwave Backhaul
- Power: Telecom DC/DC Module: Analog and Digital
- Private Branch Exchanges (PBX)
- **TETRA Base Exchanges**
- Telecom Base Band Units
- Telecom Shelters: Power Distribution Units (PDU), Power Monitoring Units (PMU), Wireless Battery Monitoring, Remote Electrical Tilt Units (RET), Remote Radio Units (RRU), Tower Mounted Amplifiers (TMA)
- Vector Signal Analyzers and Generators
- Video Conferencing: IP-Based HD
- WiMAX and Wireless Infrastructure Equipment
- Wireless Communications Testers and Wireless Repeaters
- xDSL Modems and DSLAM

# 3 Description

This dual 2-input positive-NAND gate is designed for 1.65-V to 5.5-V  $V_{CC}$  operation.

The SN74LVC2G00 device performs the Boolean function  $Y = \overline{A \times B}$  or  $Y = \overline{A} + \overline{B}$  in positive logic.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

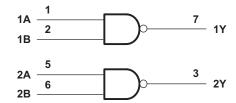
This device is fully specified for partial-power-down applications using Ioff. The Ioff circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)		
SN74LVC2G00	SM8 (8)	2.95 mm × 2.80 mm		
	US8 (8)	2.30 mm × 2.00 mm		
	DSBGA (8)	1.91 mm × 0.91 mm		

(1) For all available packages, see the orderable addendum at the end of the data sheet.

# 4 Simplified Schematic





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# 5 Revision History

#### Changes from Revision M (November 2013) to Revision N

Page

Added Applications, Device Information table, Pin Functions table, ESD Ratings table, Thermal Information table,
Typical Characteristics, Feature Description section, Device Functional Modes, Application and Implementation
section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and
Mechanical, Packaging, and Orderable Information section.

Deleted Ordering Information table.

# Changes from Revision L (January 2007) to Revision M

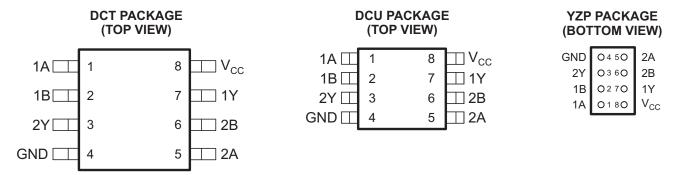
Page

•	Updated document to new TI data sheet format.	1
•	Updated operating temperature range in Recommended Operating Conditions table.	5

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# 6 Pin Configuration and Functions



See mechanical drawings for dimensions.

#### Pin Functions

F	PIN	TYPE	DESCRIPTION
NAME	DCT, DCU, YZP	ITPE	DESCRIPTION
1A	1	I	A input for gate 1
1B	2	I	B input for gate 1
2Y	3	0	Output for gate 2
GND	4	_	Ground
2A	5	I	A input for gate 2
2B	6	I	B input for gate 2
1Y	7	0	Output for gate 1
V <sub>CC</sub>	8	I	Power input.



# 7 Specifications

## 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
$V_{CC}$	Supply voltage range		-0.5	6.5	V
$V_{I}$	Input voltage range (2)	-0.5	6.5	V	
$V_{O}$	Voltage range applied to any output in the high-impeda	-0.5	6.5	V	
Vo	Voltage range applied to any output in the high or low	-0.5	V <sub>CC</sub> + 0.5	V	
I <sub>IK</sub>	Input clamp current	V <sub>I</sub> < 0		-50	mA
$I_{OK}$	Output clamp current	V <sub>O</sub> < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V <sub>CC</sub> or GND		±100	mA	
T <sub>stg</sub>	Storage temperature range	-65	150	°C	

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 7.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins (1)	2000	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101, all pins <sup>(2)</sup>	1000	V

1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

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<sup>(2)</sup> The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

<sup>(3)</sup> The value of V<sub>CC</sub> is provided in the *Recommended Operating Conditions* table.



# 7.3 Recommended Operating Conditions

			MIN	MAX	UNIT	
.,	Complexionality	Operating	1.65	5.5	V	
$V_{CC}$	Supply voltage	Data retention only	1.5		V	
		V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>			
V	High lavel input valtage	V <sub>CC</sub> = 2.3 V to 2.7 V	1.7			
$V_{IH}$	High-level input voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V	
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>			
		V <sub>CC</sub> = 1.65 V to 1.95 V		0.35 × V <sub>CC</sub>		
.,		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	.,	
$V_{IL}$	Low-level input voltage		0.8	V		
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		0.3 × V <sub>CC</sub>		
VI	Input voltage	'	0	5.5	V	
Vo	Output voltage		0	V <sub>CC</sub>	V	
		V <sub>CC</sub> = 1.65 V		-4		
		V <sub>CC</sub> = 2.3 V		-8		
I <sub>OH</sub>	High-level output current	ah-level output current		-16	mA	
		V <sub>CC</sub> = 3 V		-24		
		V <sub>CC</sub> = 4.5 V		-32		
		V <sub>CC</sub> = 1.65 V		4		
		V <sub>CC</sub> = 2.3 V		8		
l <sub>OL</sub>	Low-level output current			16	mA	
-	·	V <sub>CC</sub> = 3 V		24		
		V <sub>CC</sub> = 4.5 V		32		
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20		
Δt/Δν	Input transition rise or fall rate	V <sub>CC</sub> = 3.3 V ± 0.3 V		10	ns/V	
	·	$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5		
T <sub>A</sub>	Operating free-air temperature	1 55	-40	125	°C	

<sup>(1)</sup> All unused inputs of the device must be held at  $V_{CC}$  or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

#### 7.4 Thermal Information

			SN74LVC1G00				
	THERMAL METRIC <sup>(1)</sup>	DCT	DCU	YZP	UNIT		
		DCT         DCU         YZP         UNIT           5 PINS         5 PINS         5 PINS					
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	220	227	102	°C/W		

(1) For more information about traditional and new thermal metrics, see the IC Package Thermal Metrics application report, SPRA953.



#### 7.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETER	TEST SOURITIONS	.,	-40°C	to 85°C		-40°C	to 125°C			
PARAMETER	TEST CONDITIONS	V <sub>cc</sub>	MIN	TYP <sup>(1)</sup>	MAX	MIN	TYP <sup>(1)</sup>	MAX		
	I <sub>OH</sub> = -100 μA	1.65 V to 5.5 V	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1				
	I <sub>OH</sub> = -4 mA	1.65 V	1.2			1.2				
V	I <sub>OH</sub> = -8 mA	2.3 V	1.9			1.9			V	
V <sub>OH</sub>	$I_{OH} = -16 \text{ mA}$	3 V	2.4			2.4			V	
	$I_{OH} = -24 \text{ mA}$	3 V	2.3			2.3				
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8			3.8				
	I <sub>OL</sub> = 100 μA	1.65 V to 5.5 V		0.1				0.1	.1	
	I <sub>OL</sub> = 4 mA	1.65 V			0.45			0.45	-5	
V	I <sub>OL</sub> = 8 mA	2.3 V			0.3			0.3	V	
V <sub>OL</sub>	I <sub>OL</sub> = 16 mA	3 V			0.4			0.4	V	
	I <sub>OL</sub> = 24 mA	3 V			0.55			0.55		
	I <sub>OL</sub> = 32 mA	4.5 V			0.55			0.55		
I <sub>I</sub> A or B inputs	V <sub>I</sub> = 5.5 V or GND	0 to 5.5 V			±5			±5	μΑ	
I <sub>off</sub>	$V_I$ or $V_O = 5.5 \text{ V}$	0			±10			±10	μA	
I <sub>cc</sub>	$V_I = 5.5 \text{ V or GND},  I_O = 0$	1.65 V to 5.5 V			10			10	μΑ	
ΔI <sub>CC</sub>	One input at V <sub>CC</sub> – 0.6 V, Other inputs at V <sub>CC</sub> or GND	3 V to 5.5 V			500			500	μΑ	
C <sub>I</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	3.3 V		5					pF	

<sup>(1)</sup> All typical values are at  $V_{CC}$  = 3.3 V,  $T_A$  = 25°C.

# 7.6 Electrical Characteristics (Continued)

 $T_A = 25^{\circ}C$ 

	PARAMETER	TEST CONDITIONS	V <sub>CC</sub> = 1.8 V	V <sub>CC</sub> = 2.5 V	V <sub>CC</sub> = 3.3 V	V <sub>CC</sub> = 5 V	UNIT
	PARAMETER	TEST CONDITIONS	TYP	TYP	TYP	TYP	UNIT
Cp	d Power dissipation capacitance	f = 10 MHz	19	19	20	22	pF

## 7.7 Switching Characteristics, -40°C to 85°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

						-40°C t	o 85°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = ' ± 0.1		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = ± 0.9		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	3.7	8.6	1.6	4.8	1.1	4.3	1	3.3	ns

## 7.8 Switching Characteristics, -40°C to 125°C

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 3)

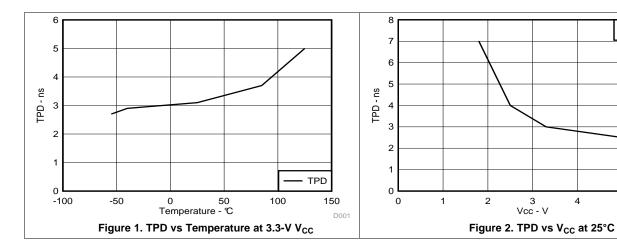
						-40°C to	o 125°C				
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V <sub>CC</sub> = 1 ± 0.15		V <sub>CC</sub> = 2 ± 0.2		V <sub>CC</sub> = 3 ± 0.3		V <sub>CC</sub> = ± 0.5		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t <sub>pd</sub>	A or B	Y	3.7	9.4	1.6	5.5	1.1	4.9	1	3.8	ns

- TPD

6



# 7.9 Typical Characteristics

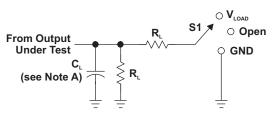


Product Folder Links: SN74LVC2G00

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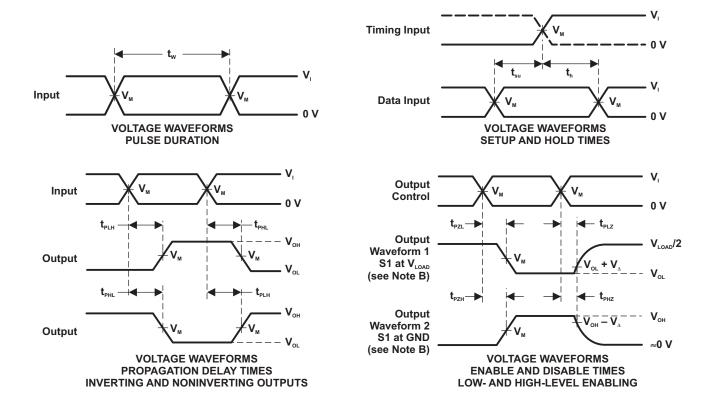
#### 8 Parameter Measurement Information



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	$\mathbf{V}_{LOAD}$
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

LOAD CIRCUIT

.,	INI	PUTS		V		-	.,
V <sub>cc</sub>	V,	t,/t,	V <sub>M</sub>	<b>V</b> <sub>LOAD</sub>	C <sub>∟</sub>	R <sub>⊾</sub>	V <sub>A</sub>
1.8 V ± 0.15 V	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	<b>1 k</b> Ω	0.15 V
$2.5~V~\pm~0.2~V$	V <sub>cc</sub>	≤2 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	30 pF	500 Ω	0.15 V
$3.3 \text{ V} \pm 0.3 \text{ V}$	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V <sub>cc</sub>	≤2.5 ns	V <sub>cc</sub> /2	2 × V <sub>cc</sub>	50 pF	500 Ω	0.3 V



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{o}$  = 50  $\Omega$ .
- D. The outputs are measured one at a time, with one transition per measurement.
- E.  $t_{\mbox{\tiny PLZ}}$  and  $t_{\mbox{\tiny PHZ}}$  are the same as  $t_{\mbox{\tiny dis}}.$
- F.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{en}$ .
- G.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{pd}$ .
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms

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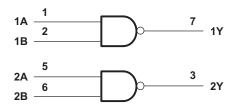


# 9 Detailed Description

#### 9.1 Overview

The  $\underline{SN74LVC2G00}$  device contains two 2-input positive-NAND gates and performs the Boolean function  $Y = \overline{A \times B}$  or  $Y = \overline{A} + \overline{B}$  on each gate. This device is fully specified for partial-power-down applications using  $I_{off}$ . The  $I_{off}$  circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

# 9.2 Functional Block Diagram



#### 9.3 Feature Description

- · Wide operating voltage range.
  - Operates from 1.65 V to 5.5 V
- Allows down voltage translation
  - Inputs accept voltages to 5.5 V
- I<sub>off</sub> feature
  - Allows voltages on the inputs and outputs, when V<sub>CC</sub> is 0 V

#### 9.4 Device Functional Modes

**Table 1. Function Table (Each Gate)** 

INPL	JTS	OUTPUT
Α	В	Υ
Н	Н	L
L	X	Н
X	L	Н

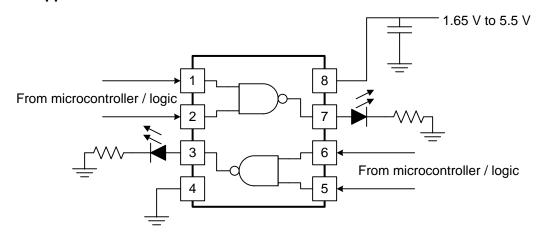


# 10 Application and Implementation

#### 10.1 Application Information

SN74LVC2G00 is a high-drive CMOS device that can be used for implementing NAND logic with a high output drive, such as an LED application. It can produce 24 mA of drive current at 3.3 V, making it Ideal for driving multiple outputs and good for high speed applications up to 100 MHz. The inputs are 5.5-V tolerant, allowing it to translate down to  $V_{\rm CC}$ .

# 10.2 Typical Application



#### 10.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Care should be taken to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

#### 10.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
  - For rise time and fall time specifications, see (Δt/ΔV) in the Recommended Operating Conditions table.
  - For specified high and low levels, see (V<sub>IH</sub> and V<sub>IL</sub>) in the Recommended Operating Conditions table.
  - Inputs are overvoltage tolerant allowing them to go as high as (V<sub>I</sub> max) in the Recommended Operating
     Conditions table at any valid V<sub>CC</sub>.

#### 2. Recommend Output Conditions

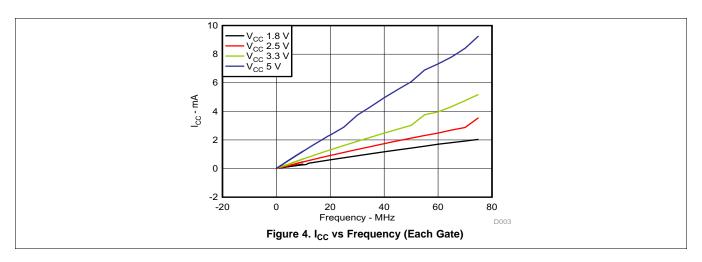
- Load currents should not exceed (I<sub>O</sub> max) per output and should not exceed total current (continuous current through V<sub>CC</sub> or GND) for the part. These limits are located in the *Absolute Maximum Ratings* table.
- Outputs should not be pulled above V<sub>CC</sub>.

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# **Typical Application (continued)**

#### 10.2.3 Application Curves



# 11 Power Supply Recommendations

The power supply can be any voltage between the min and max supply voltage rating located in the *Recommended Operating Conditions* table.

Each  $V_{CC}$  pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply a 0.1- $\mu$ F capacitor is recommended and if there are multiple  $V_{CC}$  pins then a 0.01- $\mu$ F or 0.022- $\mu$ F capacitor is recommended for each power pin. It is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- $\mu$ F and 1- $\mu$ F capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.



# 12 Layout

#### 12.1 Layout Guidelines

When using multiple bit logic devices, inputs should not float. In many cases, functions or parts of functions of digital logic devices are unused. Some examples are when only two inputs of a triple-input AND gate are used, or when only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states.

Specified in Figure 5 are the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient.

#### 12.2 Layout Example

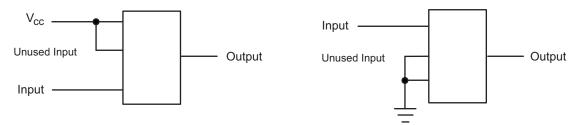


Figure 5. Layout Diagram

# 13 Device and Documentation Support

#### 13.1 Trademarks

NanoFree is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 13.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 13.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms and definitions.

# 14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.





10-Dec-2020

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G00DCT3	ACTIVE	SM8	DCT	8	3000	RoHS & Non-Green	SNBI	Level-1-260C-UNLIM	-40 to 125	C00 Z	Samples
SN74LVC2G00DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C00 (R, Z)	Samples
SN74LVC2G00DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C00 (R, Z)	Samples
SN74LVC2G00DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(C00J, C00Q, C00R)	Samples
SN74LVC2G00DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU   SN	Level-1-260C-UNLIM	-40 to 125	(C00J, C00Q, C00R)	Samples
SN74LVC2G00DCUTG4	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C00R	Samples
SN74LVC2G00YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 125	CAN	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



# **PACKAGE OPTION ADDENDUM**

10-Dec-2020

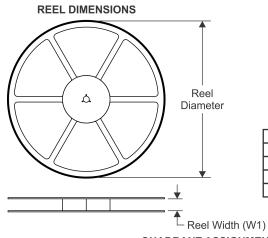
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

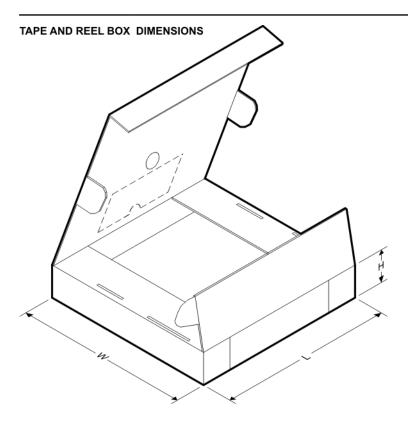


#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC2G00DCT3	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G00DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74LVC2G00DCTR	SM8	DCT	8	3000	177.8	12.4	3.45	4.4	1.45	4.0	12.0	Q3
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00DCUT	VSSOP	DCU	8	250	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00DCUT	VSSOP	DCU	8	250	178.0	9.0	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00DCUTG4	VSSOP	DCU	8	250	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74LVC2G00YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



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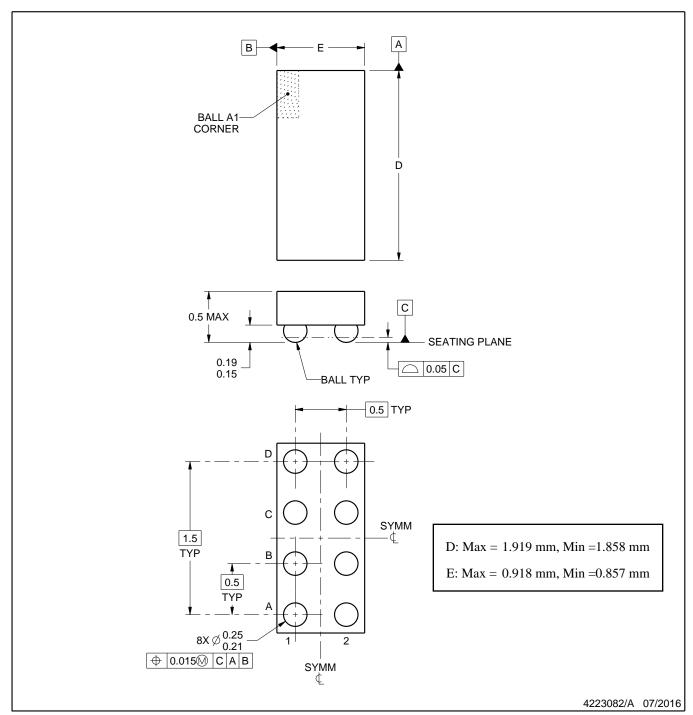


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC2G00DCT3	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G00DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74LVC2G00DCTR	SM8	DCT	8	3000	183.0	183.0	20.0
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	180.0	180.0	18.0
SN74LVC2G00DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74LVC2G00DCUT	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G00DCUT	VSSOP	DCU	8	250	180.0	180.0	18.0
SN74LVC2G00DCUTG4	VSSOP	DCU	8	250	202.0	201.0	28.0
SN74LVC2G00YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0



DIE SIZE BALL GRID ARRAY



#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



# DCU (R-PDSO-G8)

# PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.





SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.



SMALL OUTLINE PACKAGE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.



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